Lattice Semiconductor Corporation - ICE40LP384-CM36TR Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	48
Number of Logic Elements/Cells	384
Total RAM Bits	-
Number of I/O	25
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	36-VFBGA
Supplier Device Package	36-UCBGA (2.5x2.5)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40lp384-cm36tr

Table 1-1. iCE40 Family Selection Guide (continued)

84 QFN (7 mm x 7 mm, 0.5 mm)	QN84			67(7)[1]					
100 VQFP (14 mm x 14 mm, 0.5 mm)	VQ100						72(9)[1]		
121 ucBGA (5 mm x 5 mm, 0.4 mm)	CM121			95(12)	93(13)	93(13)			
121 csBGA (6 mm x 6 mm, 0.5 mm)	CB121			92(12)					
121 caBGA (9 mm x 9 mm, 0.8 mm)	BG121							93(13)	93(13)
132 csBGA (8 mm x 8 mm, 0.5 mm)	CB132						95(11)	95(12)	95(12)
144 TQFP (20 mm x 20 mm, 0.5 mm)	TQ144						96(12)	107(14)	
225 ucBGA (7 mm x 7 mm, 0.4 mm)	CM225				178(23)	178(23)			178(23)
256-ball caBGA (14 mm x 14 mm, 0.8 mm)	CT256								206(26)

1. No PLL available on the 16 WLCSP, 36 ucBGA, 81 csBGA, 84 QFN and 100 VQFP packages.
2. Only one PLL available on the 81 ucBGA package.
3. High Current I/Os only available on the 16 WLCSP package.

Introduction

The iCE40 family of ultra-low power, non-volatile FPGAs has five devices with densities ranging from 384 to 7680 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic, these devices feature Embedded Block RAM (EBR), Non-volatile Configuration Memory (NVCM) and Phase Locked Loops (PLLs). These features allow the devices to be used in low-cost, high-volume consumer and system applications. Select packages offer High-Current drivers that are ideal to drive three white LEDs, or one RGB LED.

The iCE40 devices are fabricated on a 40 nm CMOS low power process. The device architecture has several features such as programmable low-swing differential I/Os and the ability to turn off on-chip PLLs dynamically. These features help manage static and dynamic power consumption, resulting in low static power for all members of the family. The iCE40 devices are available in two versions – ultra low power (LP) and high performance (HX) devices.

The iCE40 FPGAs are available in a broad range of advanced halogen-free packages ranging from the space saving 1.40x1.48 mm WLCSP to the PCB-friendly 20x20 mm TQFP. Table 1-1 shows the LUT densities, package and I/O options, along with other key parameters.

The iCE40 devices offer enhanced I/O features such as pull-up resistors. Pull-up features are controllable on a “per-pin” basis.

The iCE40 devices also provide flexible, reliable and secure configuration from on-chip NVCM. These devices can also configure themselves from external SPI Flash or be configured by an external master such as a CPU.

Lattice provides a variety of design tools that allow complex designs to be efficiently implemented using the iCE40 family of devices. Popular logic synthesis tools provide synthesis library support for iCE40. Lattice design tools use the synthesis tool output along with the user-specified preferences and constraints to place and route the design in the iCE40 device. These tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) modules, including a number of reference designs, licensed free of charge, optimized for the iCE40 FPGA family. By using these configurable soft core IP cores as standardized blocks, users are free to concentrate on the unique aspects of their design, increasing their productivity.

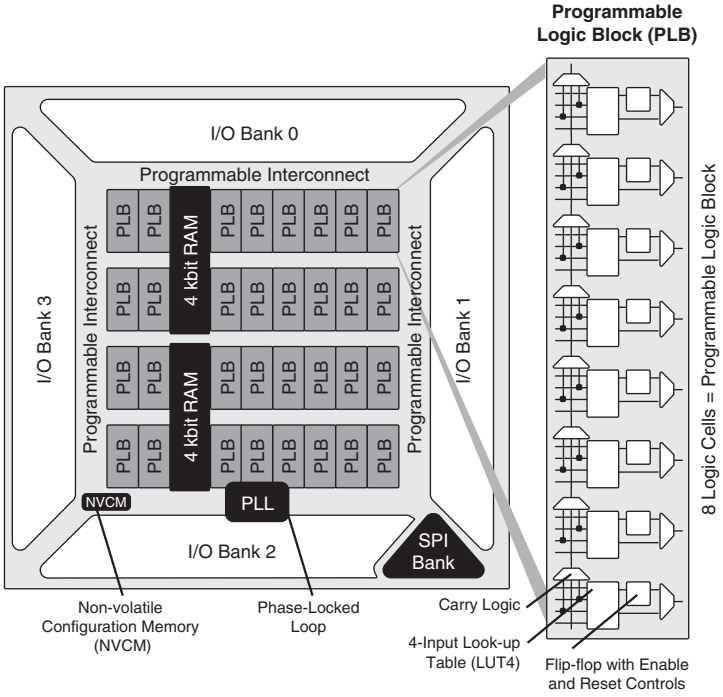
iCE40 LP/HX Family Data Sheet Architecture

March 2017 Data Sheet DS1040

Architecture Overview

The iCE40 family architecture contains an array of Programmable Logic Blocks (PLB), sysCLOCK™ PLLs, Non-volatile Programmable Configuration Memory (NVCM) and blocks of sysMEM™ Embedded Block RAM (EBR) surrounded by Programmable I/O (PIO). Figure 2-1 shows the block diagram of the iCE40LP/HX1K device.

Figure 2-1. iCE40LP/HX1K Device, Top View



The logic blocks, Programmable Logic Blocks (PLB) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each column has either logic blocks or EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PLB contains the building blocks for logic, arithmetic, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the iCE40 family, there are up to four independent sysIO banks. Note on some packages V_{CCIO} banks are tied together. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large 4 kbit, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO.

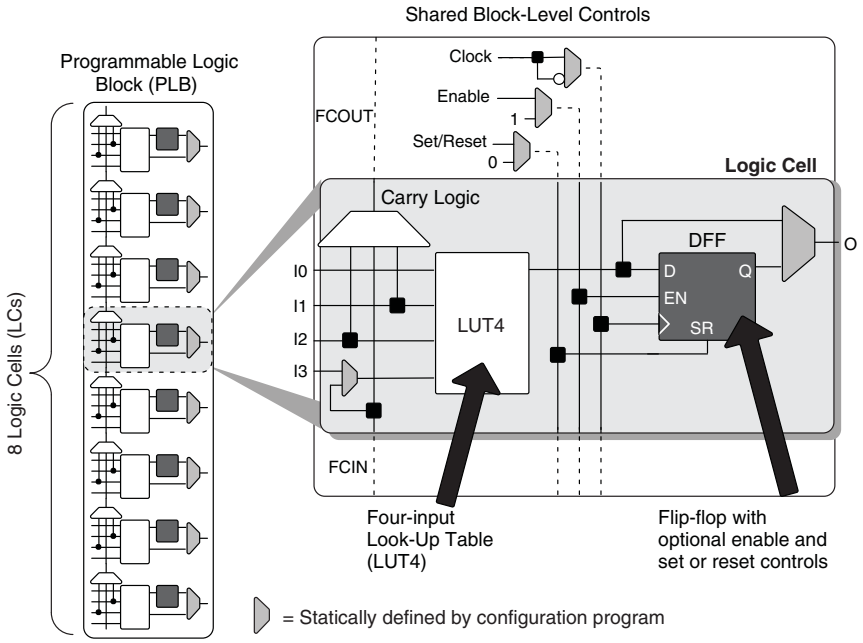
The iCE40 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

Every device in the family has a SPI port that supports programming and configuration of the device. The iCE40 includes on-chip, Nonvolatile Configuration Memory (NVCM).

PLB Blocks

The core of the iCE40 device consists of Programmable Logic Blocks (PLB) which can be programmed to perform logic and arithmetic functions. Each PLB consists of eight interconnected Logic Cells (LC) as shown in Figure 2-2. Each LC contains one LUT and one register.

Figure 2-2. PLB Block Diagram



Logic Cells

Each Logic Cell includes three primary logic elements shown in Figure 2-2.

- A four-input Look-Up Table (LUT4) builds any combinational logic function, of any complexity, requiring up to four inputs. Similarly, the LUT4 element behaves as a 16x1 Read-Only Memory (ROM). Combine and cascade multiple LUT4s to create wider logic functions.
- A 'D'-style Flip-Flop (DFF), with an optional clock-enable and reset control input, builds sequential logic functions. Each DFF also connects to a global reset signal that is automatically asserted immediately following device configuration.
- Carry Logic boosts the logic efficiency and performance of arithmetic functions, including adders, subtractors, comparators, binary counters and some wide, cascaded logic functions.

Table 2-1. Logic Cell Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	I0, I1, I2, I3	Inputs to LUT4
Input	Control signal	Enable	Clock enable shared by all LCs in the PLB
Input	Control signal	Set/Reset[1]	Asynchronous or synchronous local set/reset shared by all LCs in the PLB.
Input	Control signal	Clock	Clock one of the eight Global Buffers, or from the general-purpose interconnects fabric shared by all LCs in the PLB
Input	Inter-PLB signal	FCIN	Fast carry in
Output	Data signals	O	LUT4 or registered output
Output	Inter-PFU signal	FCOUT	Fast carry out

1. If Set/Reset is not used, then the flip-flop is never set/reset, except when cleared immediately after configuration.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Note the sysMEM Embedded Block RAM Memory address 0 cannot be initialized.

Memory Cascading

Larger and deeper blocks of RAM can be created using multiple EBR sysMEM Blocks.

RAM4k Block

Figure 2-4 shows the 256x16 memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array.

Figure 2-4. sysMEM Memory Primitives

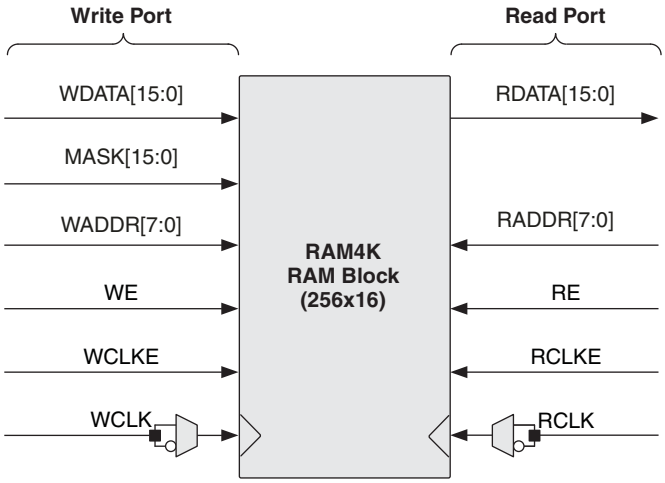


Table 2-5. EBR Signal Descriptions

Signal Name	Direction	Description
WDATA[15:0]	Input	Write Data input.
MASK[15:0]	Input	Masks write operations for individual data bit-lines. 0 = write bit; 1 = don't write bit
WADDR[7:0]	Input	Write Address input. Selects one of 256 possible RAM locations.
WE	Input	Write Enable input.
WCLKE	Input	Write Clock Enable input.
WCLK	Input	Write Clock input. Default rising-edge, but with falling-edge option.
RDATA[15:0]	Output	Read Data output.
RADDR[7:0]	Input	Read Address input. Selects one of 256 possible RAM locations.
RE	Input	Read Enable input.
RCLKE	Input	Read Clock Enable input.
RCLK	Input	Read Clock input. Default rising-edge, but with falling-edge option.

For further information on the sysMEM EBR block, please refer to TN1250, Memory Usage Guide for iCE40 Devices.

Figure 2-6. iCE I/O Register Block Diagram

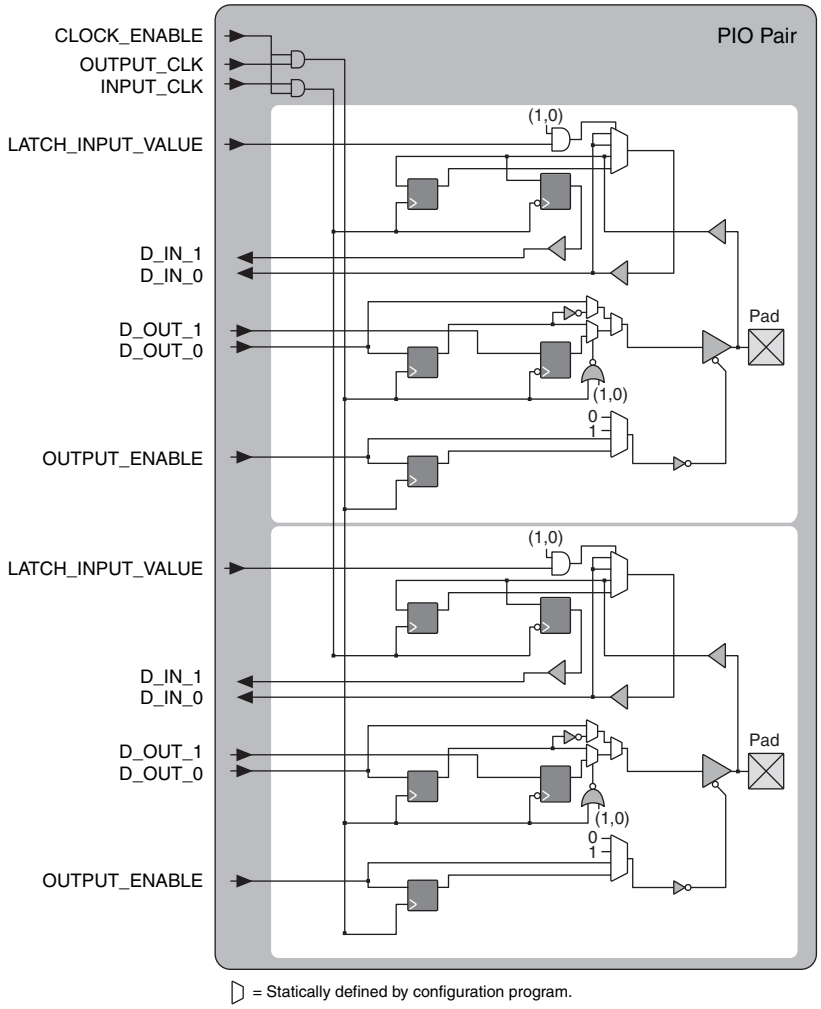


Table 2-6. PIO Signal List

Pin Name	I/O Type	Description
OUTPUT_CLK	Input	Output register clock
CLOCK_ENABLE	Input	Clock enable
INPUT_CLK	Input	Input register clock
OUTPUT_ENABLE	Input	Output enable
D_OUT_0/1	Input	Data from the core
D_IN_0/1	Output	Data to the core
LATCH_INPUT_VALUE	Input	Latches/holds the Input Value

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS and LVDS25.

High Current LED Drivers combine three sysIO buffers together. This allows for programmable drive strength. This also allows for high current drivers that are ideal to drive three white LEDs, or one RGB LED. Each bank is capable of supporting multiple I/O standards including single-ended LVCMOS buffers and differential LVDS25E output buf-

fers. Bank 3 additionally supports differential LVDS25 input buffers. Each sysIO bank has its own dedicated power supply.

Typical I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC}, V_{CCIO_2}, V_{PP_2V5}, and V_{CC_SPI} have reached the level defined in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. The default configuration of the I/O pins in a device prior to configuration is tri-stated with a weak pull-up to V_{CCIO}. The I/O pins will maintain the pre-configuration state until V_{CC} and V_{CCIO} (for I/O banks containing configuration I/Os) have reached levels, at which time the I/Os will take on the software user-configured settings only after a proper download/configuration. Unused IOs are automatically blocked and the pullup termination is disabled.

Supported Standards

The iCE40 sysIO buffer supports both single-ended and differential input standards. The single-ended standard supported is LVCMOS. The buffer supports the LVCMOS 1.8, 2.5, and 3.3 V standards. The buffer has individually configurable options for bus maintenance (weak pull-up or none). The High Current output buffer have individually configurable options for drive strength.

Table 2-7 and Table 2-8 show the I/O standards (together with their supply and reference voltages) supported by the iCE40 devices.

Table 2-7. Supported Input Standards

Input Standard	V_{CCIO} (Typical)		
	3.3 V	2.5 V	1.8 V
Single-Ended Interfaces			
LVCMOS33	Yes		
LVCMOS25		Yes	
LVCMOS18			Yes
Differential Interfaces			
LVDS25[1]		Yes	
subLVDS[1]			Yes

1. Bank 3 only.

Table 2-8. Supported Output Standards

Output Standard	V_{CCIO} (Typical)
Single-Ended Interfaces	
LVCMOS33	3.3
LVCMOS25	2.5
LVCMOS18	1.8
Differential Interfaces	
LVDS25E[1]	2.5
subLVDSE[1]	1.8

1. These interfaces can be emulated with external resistors in all devices.

Non-Volatile Configuration Memory

All iCE40 devices provide a Non-Volatile Configuration Memory (NVCM) block which can be used to configure the device.

For more information on the NVCM, please refer to TN1248, iCE40 Programming and Configuration Usage Guide.

Power On Reset

iCE40 devices have power-on reset circuitry to monitor V_{CC}, V_{CCIO_2}, V_{PP_2V5}, and V_{CC_SPI} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CC}, V_{CCIO_2}, V_{PP_2V5}, and V_{CC_SPI} (controls configuration) voltage levels. It then triggers download from the on-chip NVCM or external Flash memory after reaching the power-up levels specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration.

Programming and Configuration

This section describes the programming and configuration of the iCE40 family.

Device Programming

The NVCM memory can be programmed through the SPI port.

Device Configuration

There are various ways to configure the Configuration RAM (CRAM) including:

1. Internal NVCM Download
2. From a SPI Flash (Master SPI mode)
3. System microprocessor to drive a Serial Slave SPI port (SSPI mode)

The image to configure the CRAM can be selected by the user on power up (Cold Boot) or once powered up (Warm Boot).

For more details on programming and configuration, see TN1248, iCE40 Programming and Configuration Usage Guide.

Power Saving Options

iCE40 devices are available in two options for maximum flexibility: LP and HX devices. The LP devices have ultra low static and dynamic power consumption. HX devices are designed to provide high performance. Both the LP and the HX devices operate at 1.2 V V_{CC}.

iCE40 devices feature iCEGate and PLL low power mode to allow users to meet the static and dynamic power requirements of their applications. While these features are available in both device types, these features are mainly intended for use with iCE40 LP devices to manage power consumption.

Table 2-9. iCE40 Power Saving Features Description

Device Subsystem	Feature Description
PLL	When LATCHINPUTVALUE is enabled, forces the PLL into low-power mode; PLL output held static at last input clock value.
iCEGate	To save power, the optional iCEgate latch can selectively freeze the state of individual, non-registered inputs within an I/O bank. Registered inputs are effectively frozen by their associated clock or clock-enable control.

Power Supply Ramp Rates[1, 2]

Symbol	Parameter		Min.	Max.	Units
t_{RAMP}	Power supply ramp rates for all power supplies.	All configuration modes. No power supply sequencing.	0.40	10	V/ms
		Configuring from Slave SPI. No power supply sequencing,	0.01	10	V/ms
		Configuring from NVCM. V_{CC} and V_{PP_2V5} to be powered 0.25 ms before V_{CC_SPI}.	0.01	10	V/ms
		Configuring from MSPI. V_{CC} and V_{PP_SPI} to be powered 0.25 ms before V_{PP_2V5}.	0.01	10	V/ms

1. Assumes monotonic ramp rates.
2. iCE40LP384 requires V_{CC} to be greater than 0.7V when V_{CCIO} and V_{CC_SPI} are above GND.

Power-On-Reset Voltage Levels[1]

Symbol	Device	Parameter		Min.	Max.	Units
V_{PORUP}	iCE40LP384	Power-On-Reset ramp-up trip point (band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and VPP_2V5)	VCC	0.67	0.99	V
			VCCIO_2	0.70	1.59	V
			VCC_SPI	0.70	1.59	V
			VPP_2V5	0.70	1.59	V
	iCE40LP640, iCE40LP/HX1K, iCE40LP/HX4K, iCE40LP/HX8K	Power-On-Reset ramp-up trip point (band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and VPP_2V5)	VCC	0.55	0.75	V
			VCCIO_2	0.86	1.29	V
			VCC_SPI	0.86	1.29	V
			VPP_2V5	0.86	1.33	V
V_{PORDN}	iCE40LP384	Power-On-Reset ramp-down trip point (band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and VPP_2V5)	VCC	—	0.64	V
			VCCIO_2	—	1.59	V
			VCC_SPI	—	1.59	V
			VPP_2V5	—	1.59	V
	iCE40LP640, iCE40LP/HX1K, iCE40LP/HX4K, iCE40LP/HX8K	Power-On-Reset ramp-down trip point (band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and VPP_2V5)	VCC	—	0.75	V
			VCCIO_2	—	1.29	V
			VCC_SPI	—	1.29	V
			VPP_2V5	—	1.33	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.

ESD Performance

Please refer to the iCE40 Product Family Qualification Summary for complete qualification data, including ESD performance.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH} [1, 3, 4, 5, 6, 7]	Input or I/O Leakage	$0V < V_{IN} < V_{CCIO} + 0.2$ V	—	—	+/–10	µA
C_1 [6, 7]	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V V_{CC} = Typ., V_{IO} = 0 to V_{CCIO} + 0.2 V	—	6	—	pf
C_2 [6, 7]	Global Input Buffer Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V V_{CC} = Typ., V_{IO} = 0 to V_{CCIO} + 0.2 V	—	6	—	pf
V_{HYST}	Input Hysteresis	V_{CCIO} = 1.8 V, 2.5 V, 3.3 V	—	200	—	mV
I_{PU} [6, 7]	Internal PIO Pull-up Current	V_{CCIO} = 1.8 V, 0=<V_{IN}<=0.65 V_{CCIO}	–3	—	–31	µA
		V_{CCIO} = 2.5 V, 0=<V_{IN}<=0.65 V_{CCIO}	–8	—	–72	µA
		V_{CCIO} = 3.3 V, 0=<V_{IN}<=0.65 V_{CCIO}	–11	—	–128	µA

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Internal pull-up resistors are disabled.
2. T_J 25°C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. Only applies to IOs in the SPI bank following configuration.
5. Some products are clamped to a diode when V_{IN} is larger than V_{CCIO}.
6. High current IOs has three sysIO buffers connected together.
7. The iCE40LP640 and iCE40LP1K SWG16 package has CDONE and a sysIO buffer are connected together.

Static Supply Current – LP Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ. V_{CC}[4]	Units
I_{CC}	Core Power Supply	iCE40LP384	21	µA
		iCE40LP640	100	µA
		iCE40LP1K	100	µA
		iCE40LP4K	250	µA
		iCE40LP8K	250	µA
I_{CCPLL} [5, 6]	PLL Power Supply	All devices	0.5	µA
I_{PP_2V5}	NVCM Power Supply	All devices	1.0	µA
I_{CCIO}, I_{CC_SPI}	Bank Power Supply[4] V_{CCIO} = 2.5 V	All devices	3.5	µA

1. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.
2. Frequency = 0 MHz.
3. T_J = 25 °C, power supplies at nominal voltage.
4. Does not include pull-up.
5. No PLL available on the iCE40LP384 and iCE40LP640 device.
6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

Static Supply Current – HX Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ. V_{CC}[4]	Units
I_{CC}	Core Power Supply	iCE40HX1K	296	µA
		iCE40HX4K	1140	µA
		iCE40HX8K	1140	µA
I_{CCPLL}[5]	PLL Power Supply	All devices	0.5	µA
I_{PP_2V5}	NVCM Power Supply	All devices	1.0	µA
I_{CCIO}, I_{CC_SPI}	Bank Power Supply[4] V_{CCIO} = 2.5 V	All devices	3.5	µA

1. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.
2. Frequency = 0 MHz.
3. T_J = 25 °C, power supplies at nominal voltage.
4. Does not include pull-up.
5. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

Programming NVCM Supply Current – LP Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ. V_{CC}[5]	Units
I_{CC}	Core Power Supply	iCE40LP384	60	µA
		iCE40LP640	120	µA
		iCE40LP1K	120	µA
		iCE40LP4K	350	µA
		iCE40LP8K	350	µA
I_{CCPLL}[6, 7]	PLL Power Supply	All devices	0.5	µA
I_{PP_2V5}	NVCM Power Supply	All devices	2.5	mA
I_{CCIO}[8], I_{CC_SPI}	Bank Power Supply[5]	All devices	3.5	mA

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
2. Typical user pattern.
3. SPI programming is at 8 MHz.
4. T_J = 25 °C, power supplies at nominal voltage.
5. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up.
6. No PLL available on the iCE40-LP384 and iCE40-LP640 device.
7. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.
8. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

Programming NVCM Supply Current – HX Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ. V_{CC}[5]	Units
I_{CC}	Core Power Supply	iCE40HX1K	278	µA
		iCE40HX4K	1174	µA
		iCE40HX8K	1174	µA
I_{CCPLL}[6]	PLL Power Supply	All devices	0.5	µA
I_{PP_2V5}	NVCM Power Supply	All devices	2.5	mA
I_{CCIO}[7], I_{CC_SPI}	Bank Power Supply[5]	All devices	3.5	mA

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
2. Typical user pattern.
3. SPI programming is at 8 MHz.
4. T_J = 25 °C, power supplies at nominal voltage.
5. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up.
6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.
7. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications.

Peak Startup Supply Current – LP Devices

Symbol	Parameter	Device	Max	Units
I_{CCPEAK}	Core Power Supply	iCE40LP384	7.7	mA
		iCELP640	6.4	mA
		iCE40LP1K	6.4	mA
		iCE40LP4K	15.7	mA
		iCE40LP8K	15.7	mA
$I_{CCPLLPEAK}$[1, 2, 4]	PLL Power Supply	iCE40LP1K	1.5	mA
		iCELP640	1.5	mA
		iCE40LP4K	8.0	mA
		iCE40LP8K	8.0	mA
$I_{PP\_2V5PEAK}$	NVCM Power Supply	iCE40LP384	3.0	mA
		iCELP640	7.7	mA
		iCE40LP1K	7.7	mA
		iCE40LP4K	4.2	mA
		iCE40LP8K	4.2	mA
$I_{PP\_FASTPEAK}$[3]	NVCM Programming Supply	iCE40LP384	5.7	mA
		iCELP640	8.1	mA
		iCE40LP1K	8.1	mA
$I_{CCIOPEAK}$[5], $I_{CC\_SPIPEAK}$	Bank Power Supply	iCE40LP384	8.4	mA
		iCELP640	3.3	mA
		iCE40LP1K	3.3	mA
		iCE40LP4K	8.2	mA
		iCE40LP8K	8.2	mA

1. No PLL available on the iCE40LP384 and iCE40LP640 device.
2. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.
3. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.
4. While no PLL is available in the iCE40-LP640 the $I_{CCPLLPEAK}$ is additive to I_{CCPEAK}.
5. iCE40LP384 requires V_{CC} to be greater than 0.7 V when V_{CCIO} and V_{CC_SPI} are above GND.

SubLVDS Emulation

The iCE40 family supports the differential subLVDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all banks of the devices. The subLVDS input standard is supported by the LVDS25 differential input buffer. The scheme shown in Figure 3-2 is one possible solution for subLVDSE output standard implementation. Use LVDS25E mode with suggested resistors for subLVDSE operation. Resistor values in Figure 3-2 are industry standard values for 1% resistors.

Figure 3-2. subLVDSE

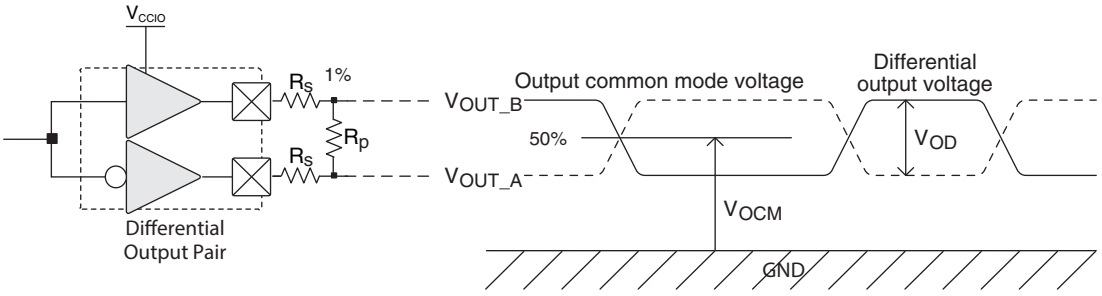


Table 3-2. subLVDSE DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	270	Ohms
R_P	Driver parallel resistor	120	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	0.9	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	2.8	mA

Typical Building Block Function Performance – LP Devices[1, 2]

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	11.0	ns
4:1 MUX	12.0	ns
16:1 MUX	13.0	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions		
16:1 MUX	190	MHz
16-bit adder	160	MHz
16-bit counter	175	MHz
64-bit counter	65	MHz
Embedded Memory Functions		
256x16 Pseudo-Dual Port RAM	240	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.

Typical Building Block Function Performance – HX Devices[1, 2]

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	10.0	ns
4:1 MUX	9.0	ns
16:1 MUX	9.5	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions		
16:1 MUX	305	MHz
16-bit adder	220	MHz
16-bit counter	255	MHz
64-bit counter	105	MHz
Embedded Memory Functions		
256x16 Pseudo-Dual Port RAM	403	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.

Over Recommended Commercial Operating Conditions - HX Devices[1, 2, 3, 4, 5]

Buffer Type	Description	Timing	Units
Input Adjusters			
LVDS25	LVDS, V_{CCIO} = 2.5 V	0.13	ns
subLVDS	subLVDS, V_{CCIO} = 1.8 V	1.03	ns
LVCMOS33	LVCMOS, V_{CCIO} = 3.3 V	0.16	ns
LVCMOS25	LVCMOS, V_{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V_{CCIO} = 1.8 V	0.23	ns
Output Adjusters			
LVDS25E	LVDS, Emulated, V_{CCIO} = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V_{CCIO} = 1.8 V	1.76	ns
LVCMOS33	LVCMOS, V_{CCIO} = 3.3 V	0.17	ns
LVCMOS25	LVCMOS, V_{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V_{CCIO} = 1.8 V	1.76	ns

1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.
2. LVCMOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. Commercial timing numbers are shown.
5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.

iCE40 External Switching Characteristics – LP Devices (Continued)[1, 2]

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
t_{HPLL}	Clock to Data Hold - PIO Input Register	iCE40LP1K	–0.90	—	ns
		iCE40LP4K	–0.80	—	ns
		iCE40LP8K	–0.80	—	ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions can be extracted from the iCECube2 software.
2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.
3. Supported on devices with a PLL.

SPI Master or NVCM Configuration Time[1, 2]

Symbol	Parameter	Conditions	Typ.	Units
t_{CONFIG}	POR/CRESET_B to Device I/O Active	iCE40LP384 - Low Frequency (Default)	25	ms
		iCE40LP384 - Medium Frequency	15	ms
		iCE40LP384 - High Frequency	11	ms
		iCE40LP640 - Low Frequency (Default)	53	ms
		iCE40LP640 - Medium Frequency	25	ms
		iCE40LP640 - High Frequency	13	ms
		iCE40LP/HX1K - Low Frequency (Default)	53	ms
		iCE40LP/HX1K - Medium Frequency	25	ms
		iCE40LP/HX1K - High Frequency	13	ms
		iCE40LP/HX4K - Low Frequency (Default)	230	ms
		iCE40LP/HX4K - Medium Frequency	110	ms
		iCE40LP/HX4K - High Frequency	70	ms
		iCE40LP/HX8K - Low Frequency (Default)	230	ms
		iCE40LP/HX8K - Medium Frequency	110	ms
		iCE40LP/HX8K - High Frequency	70	ms

1. Assumes sysMEM Block is initialized to an all zero pattern if they are used.
2. The NVCM download time is measured with a fast ramp rate starting from the maximum voltage of POR trip point.

sysCONFIG Port Timing Specifications[1] (Continued)

Symbol	Parameter		Min.	Typ.	Max.	Units
t_{MCLK}	CRESET_B high to first MCLK edge	iCE40LP384 - Low Frequency (Default)	600	—	—	us
		iCE40LP384 - Medium Frequency	600	—	—	us
		iCE40LP384 - High Frequency	600	—	—	us
		iCE40LP640, iCE40LP/HX1K - Low Frequency (Default)	800	—	—	us
		iCE40LP640, iCE40LP/HX1K - Medium Frequency	800	—	—	us
		iCE40LP640, iCE40LP/HX1K - High Frequency	800	—	—	us
		iCE40LP/HX1K -Low Frequency (Default)	800	—	—	us
		iCE40LP/HX1K - Medium Frequency	800	—	—	us
		iCE40LP/HX1K - High Frequency	800	—	—	us
		iCE40LP/HX4K - Low Frequency (Default)	1200	—	—	us
		iCE40LP/HX4K - Medium Frequency	1200	—	—	us
		iCE40LP/HX4K - high frequency	1200	—	—	us
		iCE40LP/HX8K - Low Frequency (Default)	1200	—	—	us
		iCE40LP/HX8K - Medium Frequency	1200	—	—	us
		iCE40LP/HX8K - High Frequency	1200	—	—	us

1. Does not apply for NVCM.
2. Supported only with 1.2 V V_{CC} and at 25 °C.
3. Extended range f_{MAX} Write operations support up to 53 MHz only with 1.2 V V_{CC} and at 25 °C.

Pin Information Summary

	iCE40LP384			iCE40LP640	iCE40LP1K							
	SG32	CM36[2]	CM49[2]	SWG16	SWG16	CM36[1, 2]	CM49[1, 2]	CM81	CB81	QN84	CM121	CB121
General Purpose I/O per Bank												
Bank 0	6	4	10	3	3	4	10	17	17	17	24	24
Bank 1	5	7	7	0	0	7	7	15	16	17	25	21
Bank 2	0	4	4	1	1	4	4	11	8	11	18	19
Bank 3	6	6	12	2	2	6	10	16	17	18	24	24
Configuration	4	4	4	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	21	25	37	10	10	25	35	63	62	67	95	92
High Current Outputs per Bank												
Bank 0	0	0	0	3	3	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0
Total Current Outputs	0	0	0	3	3	0	0	0	0	0	0	0
Differential Inputs per Bank												
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	3	3	6	1	1	3	5	8	9	7	12	12
Total Differential Inputs	3	3	6	1	1	3	5	8	9	7	12	12
Dedicated Inputs per Bank												
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	2	2	2	1	1	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	2	1	1	2	2	2	2	2	2	2
Vccio Pins												
Bank 0	1	1	1	1	1	1	1	1	1	1	2	1
Bank 1	1	1	1	0	0	0	0	1	1	1	2	1
Bank 2	1	1	1	1	1	1	1	1	1	1	2	1
Bank 3	1	0	0	0	0	0	0	1	1	1	2	2
VCC	1	1	2	1	1	1	2	3	3	4	4	4
VCC_SPI	1	1	1	0	0	1	1	1	1	1	1	1
VPP_2V5	1	1	1	0	0	1	1	1	1	1	1	1
VPP_FAST[3]	0	0	0	0	0	1	1	1	0	1	1	1
VCCPLL	0	0	0	0	0	0	1	1	0	0	1	1
GND	2	3	3	2	2	3	4	5	8	4	8	11
NC	0	0	0	0	0	0	0	0	0	0	0	3
Total Count of Bonded Pins	32	36	49	16	16	36	49	81	81	84	121	121

1. V_{CCIO0} and V_{CCIO1} are connected together.
2. V_{CCIO2} and V_{CCIO3} are connected together.
3. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP8K-CM121TR1K	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND

High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40HX1K-CB132	1280	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX1K-VQ100	1280	1.2 V	Halogen-Free VQFP	100	IND
ICE40HX1K-TQ144	1280	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX4K-BG121	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-BG121TR	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-CB132	3520	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX4K-TQ144	3520	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX8K-BG121	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-BG121TR	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-CB132	7680	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND
ICE40HX8K-CT256	7680	1.2 V	Halogen-Free caBGA	256	IND

Date	Version	Section	Change Summary
April 2013	02.2	Introduction	Added the LP8K 81 ucBGA.
		Architecture	Corrected typos.
		DC and Switching Characteristics	Corrected typos. Added 7:1 LVDS waveforms.
		Pinout Information	Corrected typos in signal descriptions. Added the LP8K 81 ucBGA.
		Ordering Information	Added the LP8K 81 ucBGA.
March 2013	02.1	DC and Switching Characteristics	Recommended operating conditions added requirement for Master SPI.
			Updated Recommended Operating Conditions for V_{PP_2V5}.
			Updated Power-On-Reset Voltage Levels and sequence requirements.
			Updated Static Supply Current conditions.
			Changed unit for t_{SKEW_IO} from ns to ps.
			Updated range of CCLK f_{MAX}.
		Ordering Information	Updated ordering information to include tape and reel part numbers.
September 2012	02.0	—	Merged SiliconBlue iCE40 LP and HX data sheets and updated to Lattice format.
	01.31	—	Updated Table 1.
	01.3	—	Production release.
			Updated notes on Table 3: Recommended Operating Conditions.
			Updated values in Table 4, Table 5, Table 12, Table 13 and Table 17.
	01.21	—	Updated Figure 3 and Figure 4 to specify iCE40.
Aug 2012	01.2	—	Updated company name.
July 2011	01.1	—	Moved package specifications to iCE40 pinout Excel files.
			Updated Table 1 maximum I/Os.
	01.01	—	Added 640, 1K and 4K to Table 13 configuration times. Updated Table 1 maximum I/Os.
	01.0	—	Initial release.